15. An epitaxial growth method comprising:

directly heating a substrate by a radiation source without using any heat sink material;

supplying a set of reactant species on one side of the substrate for growing an epitaxial layer on the first side of the substrate at an elevated temperature; and

without cooling down to room temperature, supplying another set of reactant species on the other side of the substrate for growing an epitaxial layer on an opposing side of the substrate.

18. A heating method comprising directly heating a semiconductor layered substrate by a radiation source without using any heat sink material, wherein each layer of the semiconductor layered substrate has a different thermal expansion coefficient.

19. An epitaxial growth method comprising:

placing a substrate in a system so that each side of the substrate is not completely covered by any parts or susceptor blocks;

directly heating the substrate by a radiation source without using any heat sink material;

supplying a set of reactant species on one side of the substrate;

supplying another set of reactant species on the other side of the substrate; and

preventing mixing of the two sets of reactant species.

SEE APPENDIX FOR CHANGES MADE TO THE CLAIMS

Please add the following new claims:

--24. The epitaxial growth method of claim 11 further comprising the step of removing the layered substrate after growing the epitaxial layer.

25. The epitaxial growth method of claim 24 wherein the step of removing comprises mechanical polishing.

26. The epitaxial growth method of claim 11 wherein a process of forming said layered substrate includes a heating step, wherein said layered substrate exhibits the bowing after being cooled down from said heating step.

27. The epitaxial growth method of claim 15, further comprising the step of preventing mixing of the two sets of reactant species.

28. The epitaxial growth method of claim 11, wherein the step of growing an epitaxial layer on a layered substrate which exhibits bowing is conducted so as to flatten said bowed layered substrate.--

REMARKS

I. CLAIM 18 IS DEFINITE

Claim 18 stands rejected under 35 U.S.C. § 112, second paragraph. This rejection is respectfully traversed for the following reasons. The Examiner first alleges that "[i]t is unclear in claim 18 whether the radiation source or the layered substrate is without a heat